

P-Channel MOSFET

2SJ360

■ Electrical Characteristics Ta = 25°C

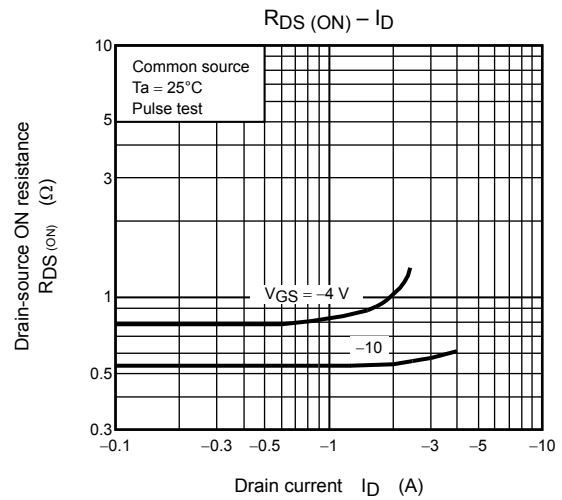
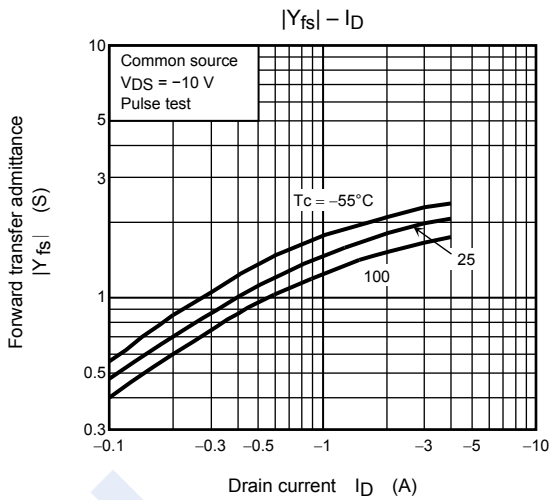
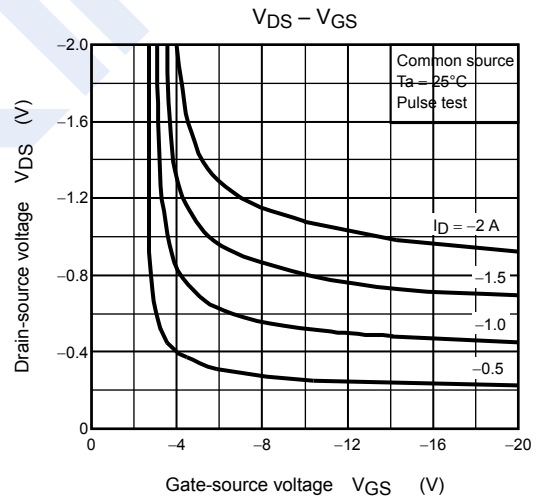
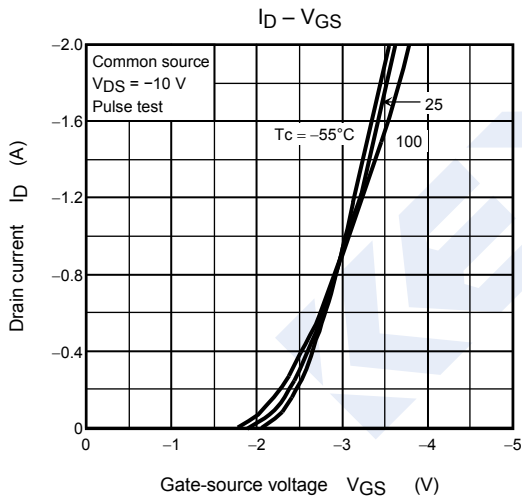
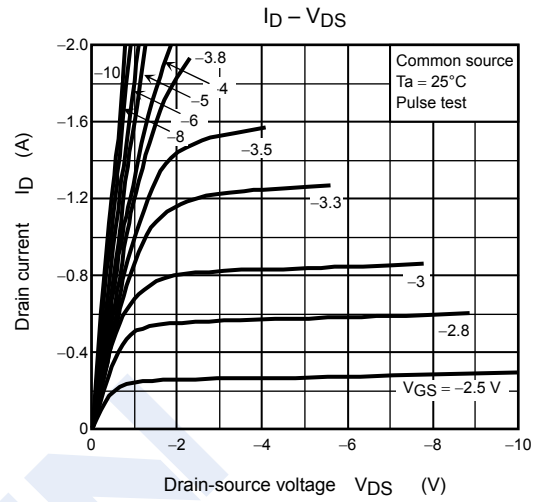
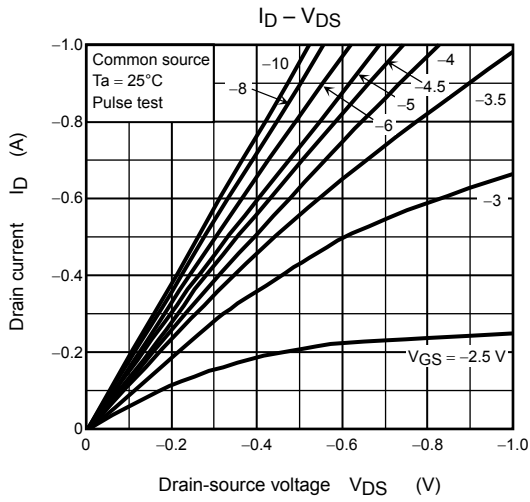
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
Drain-Source Breakdown Voltage	V_{DS}	$I_D = -10\text{mA}$, $V_{GS} = 0\text{V}$	-60			V	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60\text{V}$, $V_{GS} = 0\text{V}$			-100	μA	
Gate-Body leakage current	I_{GSS}	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 16\text{V}$			± 10	μA	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = -10\text{V}$, $I_D = -1\text{mA}$	-0.8		-2	V	
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4\text{V}$, $I_D = -0.5\text{A}$			1.2	Ω	
		$V_{GS} = -10\text{V}$, $I_D = -0.5\text{A}$			0.73		
Forward Transconductance	g_{FS}	$V_{DS} = -10\text{V}$, $I_D = -0.5\text{A}$	0.5	1		S	
Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = -10\text{V}$, $f = 1\text{MHz}$		155		pF	
Output Capacitance	C_{oss}			22			
Reverse Transfer Capacitance	C_{rss}			75			
Total Gate Charge	Q_g			6.5			
Gate Source Charge	Q_{gs}	$V_{GS} = -10\text{V}$, $V_{DS} = -48\text{V}$, $I_D = -1\text{A}$		4.5		nC	
Gate Drain Charge	Q_{gd}			2			
Turn-On Delay Time	$t_{d(on)}$			20		ns	
Turn-On Rise Time	t_r				17		
Turn-Off Delay Time	$t_{d(off)}$				100		
Turn-Off Fall Time	t_f				20		
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -1\text{A}$, $V_{GS} = 0$, $di/dt = 50\text{A}/\mu\text{s}$		50		nA	
Body Diode Reverse Recovery Charge	Q_{rr}			45			
Continuous drain reverse current	I_{DR}				-1	A	
Pulse drain reverse current	I_{DRP}				-4	A	
Diode Forward Voltage	V_{SD}	$I_{DR} = -1\text{A}$, $V_{GS} = 0\text{V}$			-1.8	V	

■ Marking

Marking	Z*8
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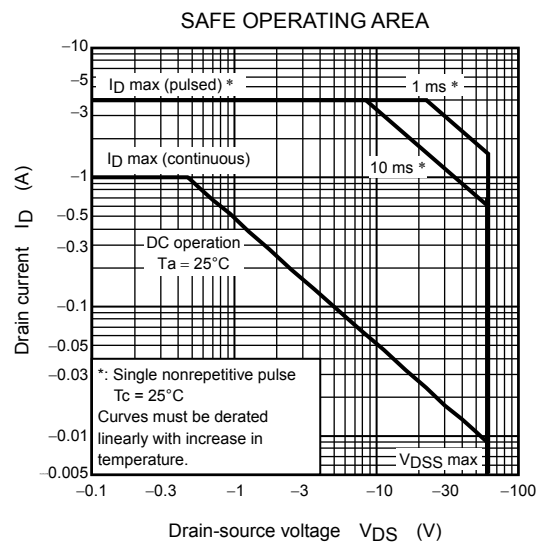
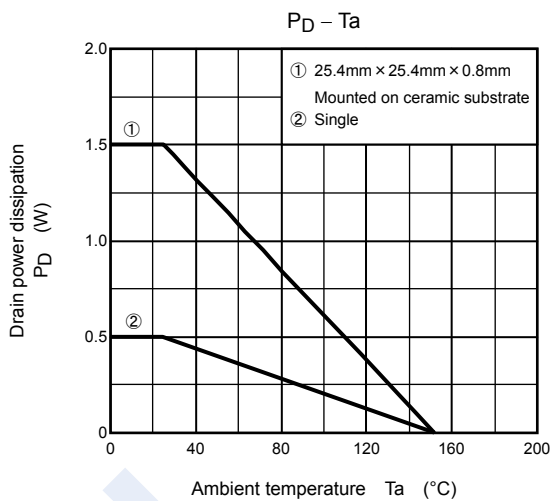
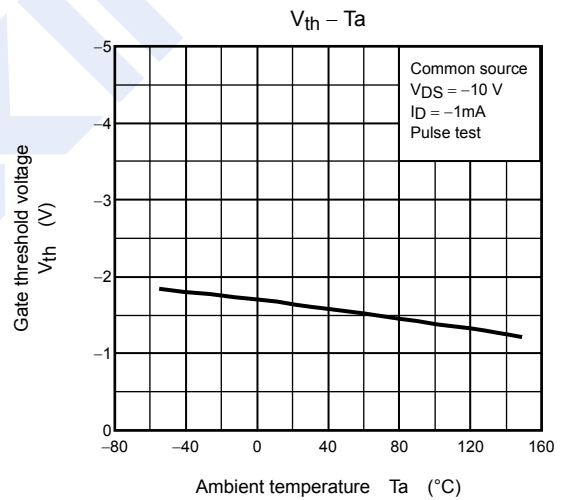
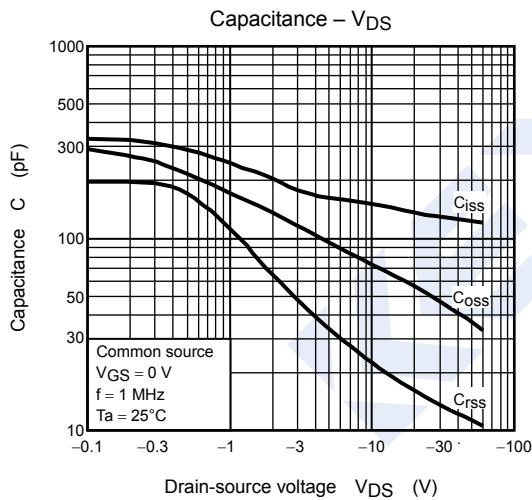
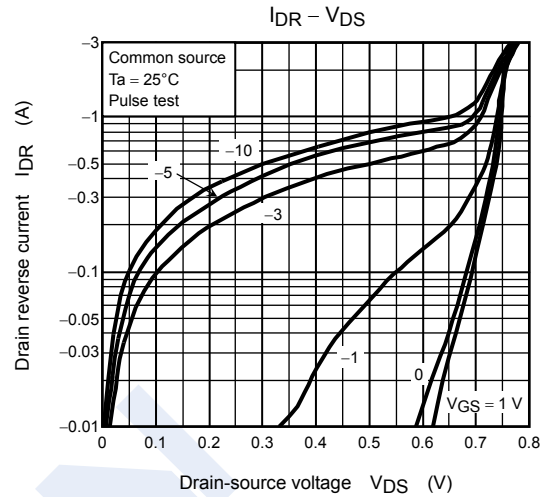
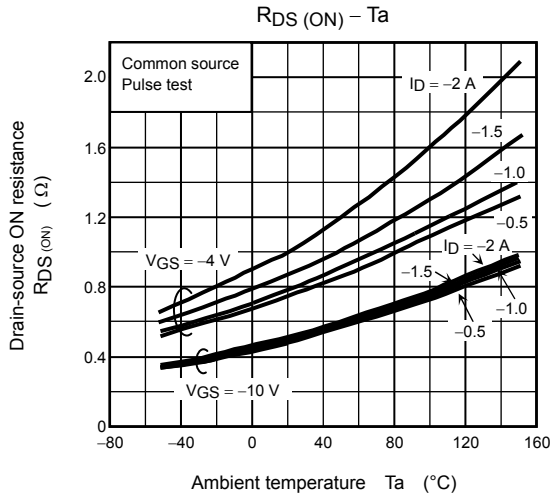
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■ Typical Characteristics



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